

- 1           1.    A method comprising:  
2                defining a pair of spaced apart floating gates  
3   over a substrate;  
4                forming a stacked control gate over each floating  
5   gate; and  
6                forming a drain and a pair of sources by  
7   implantation using said stacked control gates as a mask.
  
- 1           2.    The method of claim 1 including using said  
2   control gates to protect said floating gates from said  
3   implantation.
  
- 1           3.    The method of claim 1 including self-aligning  
2   said sources and drain to both of said control gates.
  
- 1           4.    The method of claim 1 including using substrate  
2   hot electron injection to charge said floating gates.